SUPPORTING INFORMATION

Near-Infrared Photocatalytic Activity Induced by Intrinsic Defects in Bi₂MO₆

(M=W, Mo)

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Figure S1 Energy band of (a) Bi_{vac} - Bi_2WO_6 , (b) W_{vac} - Bi_2WO_6 , (c) Bi_w - Bi_2WO_6 , (d) W_{Bi} - Bi_2WO_6 , (e) W_{int} - Bi_2WO_6 , (f) O_{int} - Bi_2WO_6 . The red dashed lines represent the Fermi level, which is set to zero.

Figure S2 Projected density of states (PDOS) of (a) Bivac-Bi2WO6, (b) Wvac-Bi2WO6,

(c) Bi_w - Bi_2WO_6 , (d) W_{Bi} - Bi_2WO_6 , (e) W_{int} - Bi_2WO_6 , (f) O_{int} - Bi_2WO_6 .

Figure S3 Energy band of (a) Bivac-Bi2MoO₆, (b) Movac-Bi2MoO₆, (c) Bi_{Mo}-Bi2MoO₆,

(d) $Mo_{Bi}-Bi_2MoO_6$, (e) $Mo_{int}-Bi_2MoO_6$, (f) $O_{int}-Bi_2MoO_6$. The red dashed lines represent the Fermi level, which is set to zero.

Figure S4 Projected density of states (PDOS) of (a) Bi_{vac} - Bi_2MoO_6 , (b) Mo_{vac} - Bi_2MoO_6 , (c) Bi_{Mo} - Bi_2MoO_6 , (d) Mo_{Bi} - Bi_2MoO_6 , (e) Mo_{int} - Bi_2MoO_6 , (f) O_{int} - Bi_2MoO_6 .



Figure S1



Figure S2





Figure S4